



scia Clean 800

HIGH-QUALITY CLEANING AND QUALIFICATION

Features & Benefits

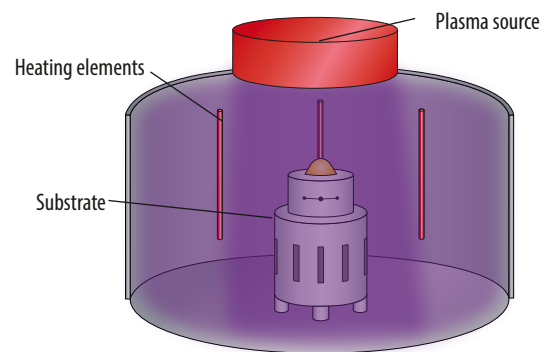
- Low base pressure and fast pumping due to electropolished and heated vacuum chamber
- Separate substrate heating for improved desorption
- Qualification of residual contamination by high-sensitive mass spectroscopy
- Optional plasma source for advanced cleaning with H₂ plasma
- Recipes for repeatable temperature ramps and fully automated cleaning cycles
- Crane for loading of large and heavy substrates

Applications

- Ultra-high purity cleaning of X-ray optics
- Cleaning of components for beam line accelerators
- Outgassing qualification of complex vacuum assemblies

Principle

- Dry-Cleaning
 - Removing of contamination from 3-dimensional shaped substrates by using ultra-high vacuum (vacuum desorption)
 - Further cleaning progress with optional heating of substrate and/or chamber (thermal desorption) and applying plasma treatment



Technical Data

Substrate size (up to)	800 mm dia., 500 mm height, 500 kg
Substrate heating	Radiation heaters (4.5 kW) up to 250 °C
Chamber heating and cooling	Pressurized water based heating up to 150 °C and cooling (8 kW)
Plasma sources	Optional ICP plasma source (PI400), max. 2.5 kW
Base pressure	< 5 x 10 ⁻⁹ mbar
Quality control	Mass spectrometer for quantitative outgassing measurement
System dimension (W x D x H)	1.30 m x 2.50 m x 1.40 m (without electrical rack and pumps)
Configuration	Single chamber with top lid, optional crane for loading of heavy substrates
Software interfaces	SECS II / GEM, OPC

